

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

2SC2873-x-MS

Product specification

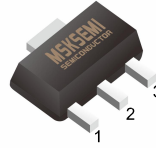
TRANSISTOR (NPN)

FEATURE

- Small Flat Package
- High Speed Switching Time
- Low Collector-emitter saturation voltage
- Complementary to 2SA1213-x-MS

Reference News

SOT-89



1. BASE
2. COLLECTOR
3. EMITTER

MARKING

2SC2873-O-MS	2SC2873-Y-MS
MO	MY

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	50	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EB0}	Emitter-Base Voltage	5	V
I _C	Collector Current	2	A
P _C	Collector Power Dissipation	500	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	250	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

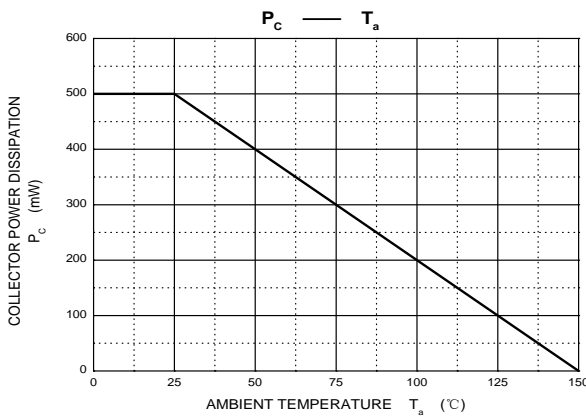
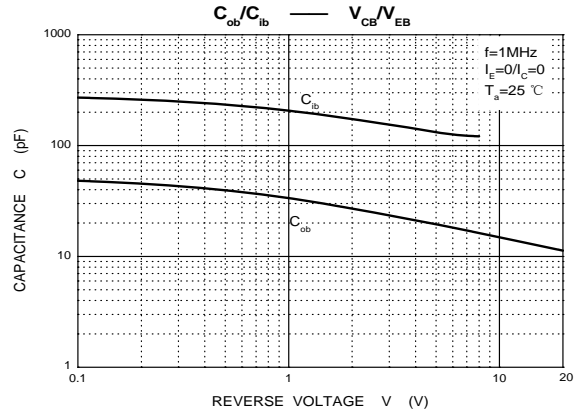
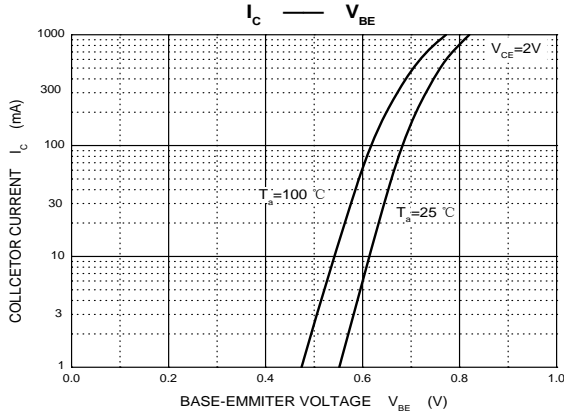
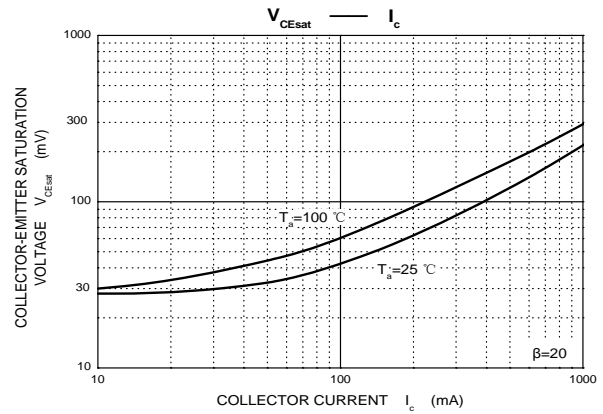
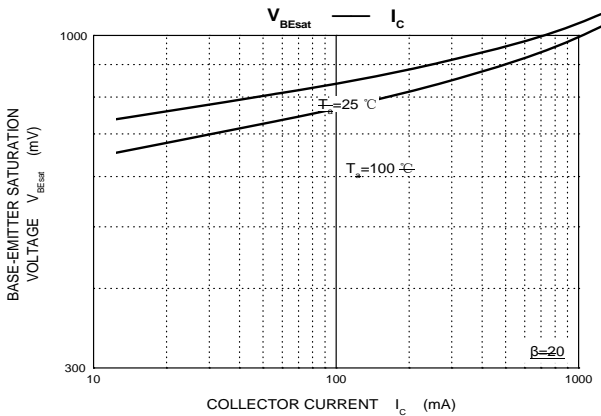
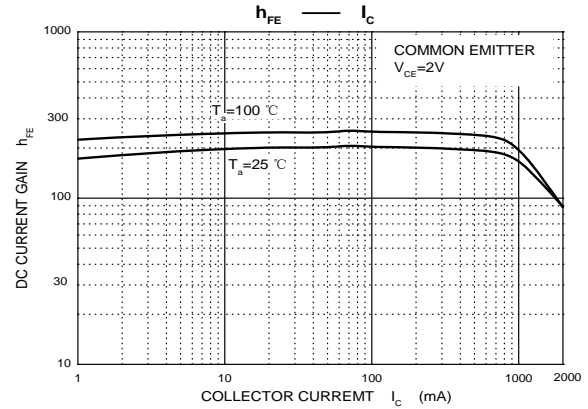
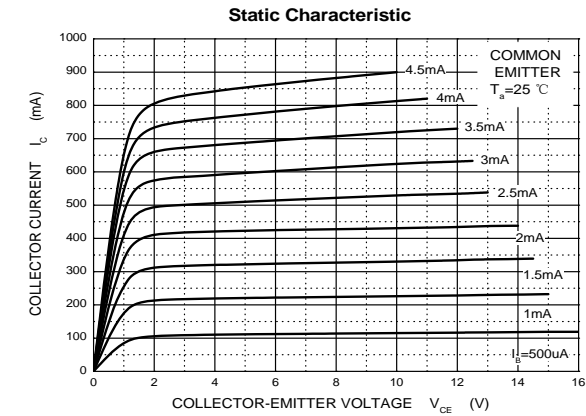
ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA, I _E =0	50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =50V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =2V, I _C =0.5A	70		240	
	h _{FE(2)}	V _{CE} =2V, I _C =2A	20			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =1A, I _B =50mA			0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =1A, I _B =50mA			1.2	V
Transition frequency	f _T	V _{CE} =2V, I _C =0.5A		120		MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		30		pF

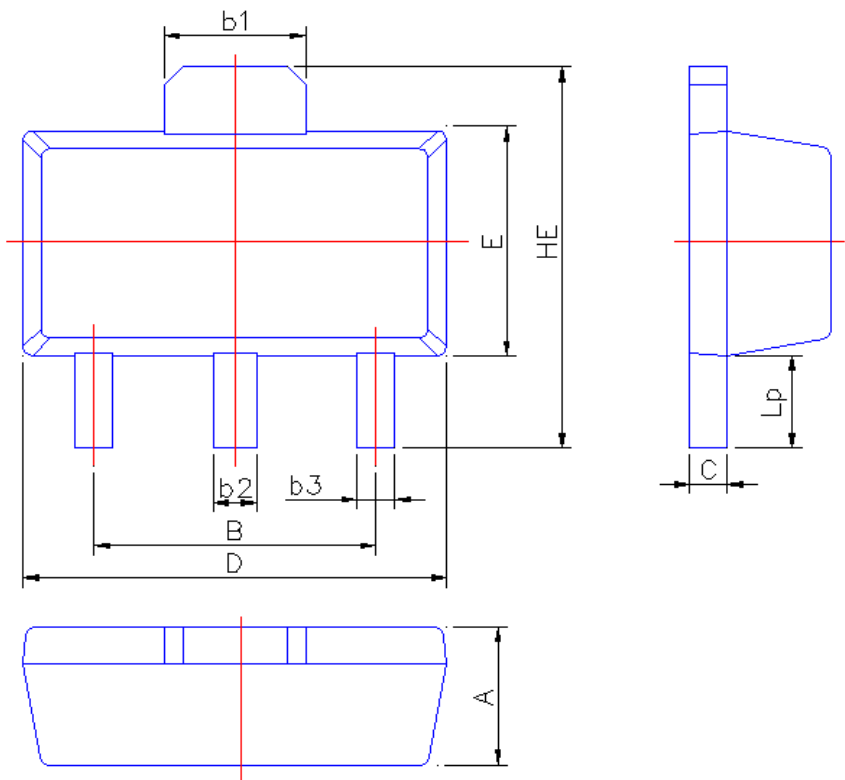
CLASSIFICATION OF h_{FE}

Rank	2SC2873-O-MS	2SC2873-Y-MS
Range	70 -140	120-240

Typical Characteristics



PACKAGE MECHANICAL DATA



SOT-89

Symbol	Dimension in Millimeters	
	Min	Max
A	1.40	1.60
B	2.95	3.05
b1	1.45	1.70
b2	0.45	0.60
b3	0.35	0.50
C	0.35	0.50
D	4.40	4.60
E	2.35	2.55
HE	3.90	4.40
Lp	0.90	1.10

REELSPECIFICATION

P/N	PKG	QTY
2SC2873-x-MS	SOT-89	1000

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